In the Claims

1. (Currently amended) A liquid CVD precursor composition for forming a thin film dielectric on a substrate, such precursor composition including at least one metalloamide source reagent compound having a formula:

$$M(NR_2)_x(NR'_2)_y$$

wherein M is selected from the group consisting of: Y, Hf, La, and Ta; N is nitrogen, each of R and R' is independently selected from the group consisting of H, aryl, perfluoroaryl, C_1-C_8 alkyl, C_1-C_8 perfluoroalkyl, and alkylsilyl; $(NR_2)_x$ and $(NR'_2)_y$ are different amino ligands and R' is different from R; x is from 1 to 5; y is from 1 to 5; and x+y is equal to the oxidation state of metal M, and a solvent medium, wherein the metalloamide source reagent compound is soluble or suspendable therein.

2. (Currently amended) The liquid CVD precursor composition according to claim 1, wherein one of the amino ligands is NMe_2.

3. (Currently amended) The liquid CVD precursor composition according to claim 1, wherein one of the amino ligands is NEt_2.

4. -7 (Cancelled)

8. (Currently amended) The liquid CVD precursor composition according to claim 1, wherein the ~~precursor composition further comprises a~~ solvent medium is selected from the group consisting of: ethers, glymes, tetraglymes, amines, polyamines, alcohols, glycols, aliphatic hydrocarbon solvents, aromatic hydrocarbon solvents, cyclic ethers and combinations of two or more of the foregoing.

9. (Cancelled)

10. (Currently amended) The liquid CVD precursor composition according to claim 8, wherein the solvent is octane.

11. (Currently amended) The liquid CVD precursor composition according to claim 1, wherein the metalloamide source reagent compound is injected by liquid delivery into a chemical vapor deposition chamber.

12. (Currently amended) The liquid CVD precursor composition according to claim 1, wherein the metalloamide source reagent compounds is delivered by bubbler into a chemical vapor deposition chamber.

13.-15. (Cancelled)

16. (Currently amended) The liquid CVD precursor composition according to claim 1, wherein the precursor composition comprises multiple metalloamide source reagent compounds.

17.-36. (Cancelled)

37. (Currently amended) A liquid CVD precursor composition for forming a thin film dielectric on a substrate, such precursor composition including a vapor source reagent mixture including a metalloamide source reagent compound having a formula:

$$M(NR_2)_x(NR'_2)_y$$

wherein M is selected from the group consisting of: Y, Hf, La, and Ta,; N is nitrogen; each of R and R' is independently selected from the group consisting of H, aryl, perfluoroaryl, C_1-C_8 alkyl, C_1-C_8 perfluoroalkyl, and alkylsilyl; $M(NR_2)_x$ and $(NR'_2)_y$ are different amino ligands and R' is different from R; x is from 1 to 5; y is from 1 to 5; and x+y is equal to the oxidation state of metal M, and a solvent medium, wherein the metalloamide source reagent compound is soluble or suspendable therein.

38.-86. (Cancelled)

87. (Withdrawn) A liquid CVD precursor composition for forming a thin film dielectric on a substrate, such precursor composition including at least one metalloamide source reagent compound having a formula:

$M(NR^1R^2)_x$

wherein M is selected from the group consisting of: Hf, Y, La, Lanthanide series elements, and Ta; N is nitrogen each of R^1 and R^2 is independently selected from the group consisting of H, aryl, perfluoroaryl, C_1-C_8 alkyl, C_1-C_8 perfluoroalkyl, and alkylsilyl; x is from 1 to 5 and equal to the oxidation state of metal M, and a solvent medium, wherein the metalloamide source reagent compound is soluble or suspendable therein.

88. (Withdrawn) The liquid CVD precursor composition of claim 87, wherein M is Ta.

89. (Withdrawn) The liquid CVD precursor composition of claim 87, wherein M is Y

90. (Withdrawn) The liquid CVD precursor composition of claim 88, selected from the group consisting of $Ta(NEt_2)_5$, $Ta(NEt_2)_5$, $Ta(NMeEt)_5$, and $Ta(NMe_2)_5$.

91. (Withdrawn) The liquid CVD precursor composition of claim 87, selected from the group consisting of $Y(NMe_2)_3$ and $Y(NEt_2)_3$.